



# NX3008PBKW

30 V, 200 mA P-channel Trench MOSFET

Rev. 1 — 1 August 2011

Product data sheet

## 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

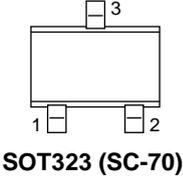
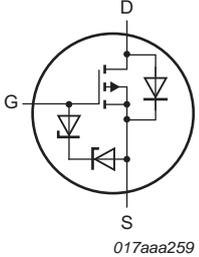
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-30	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-200	mA
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -200\text{ mA}; T_j = 25\text{ °C}$	-	2.8	4.1	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SOT323 (SC-70)</p>	 <p>017aaa259</p>
2	S	source		
3	D	drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX3008PBKW	SC-70	plastic surface-mounted package; 3 leads	SOT323

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
NX3008PBKW	AB%

[1] % = placeholder for manufacturing site code

## 5. Limiting values

**Table 5. Limiting values**

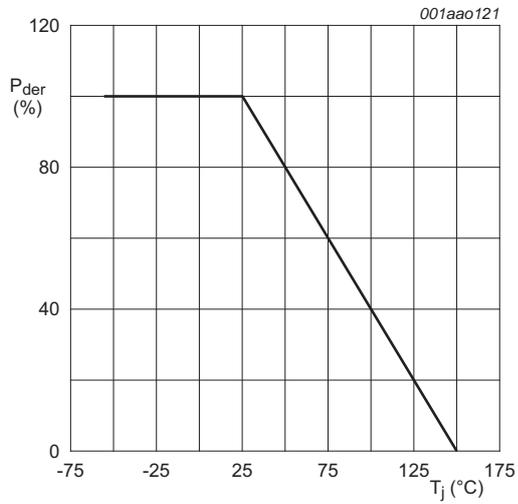
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-30	V	
$V_{GS}$	gate-source voltage		-8	8	V	
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-200	mA
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	-130	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	-0.8	A	
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	260	mW
			[1]	-	310	mW
		$T_{sp} = 25\text{ °C}$	-	-	830	mW
$T_j$	junction temperature		-55	150	°C	
$T_{amb}$	ambient temperature		-55	150	°C	
$T_{stg}$	storage temperature		-65	150	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	-200	mA
<b>ESD maximum rating</b>						
$V_{ESD}$	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

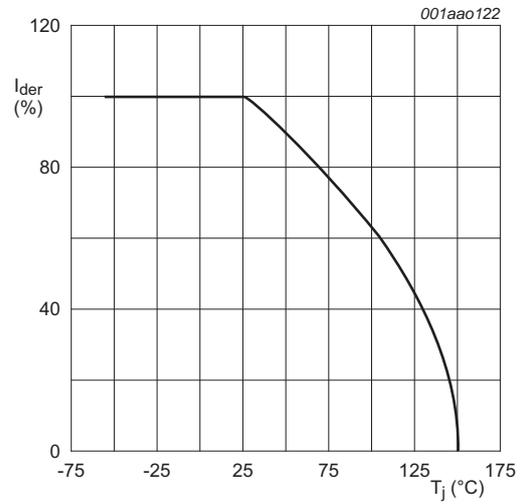
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



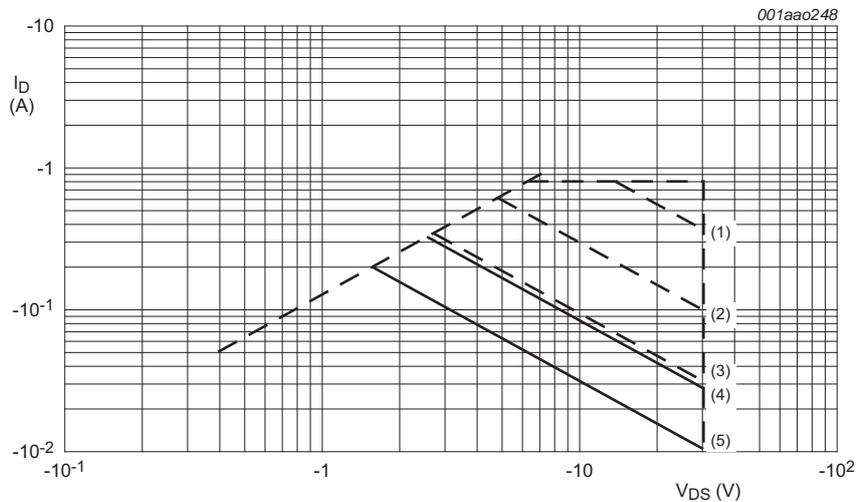
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of junction temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of junction temperature**



$I_{DM}$  is a single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3)  $t_p = 100 \text{ ms}$
- (4) DC;  $T_{sp} = 25^{\circ}C$
- (5) DC;  $T_{amb} = 25^{\circ}C$ ;  $1 \text{ cm}^2$  drain mounting pad

**Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage**

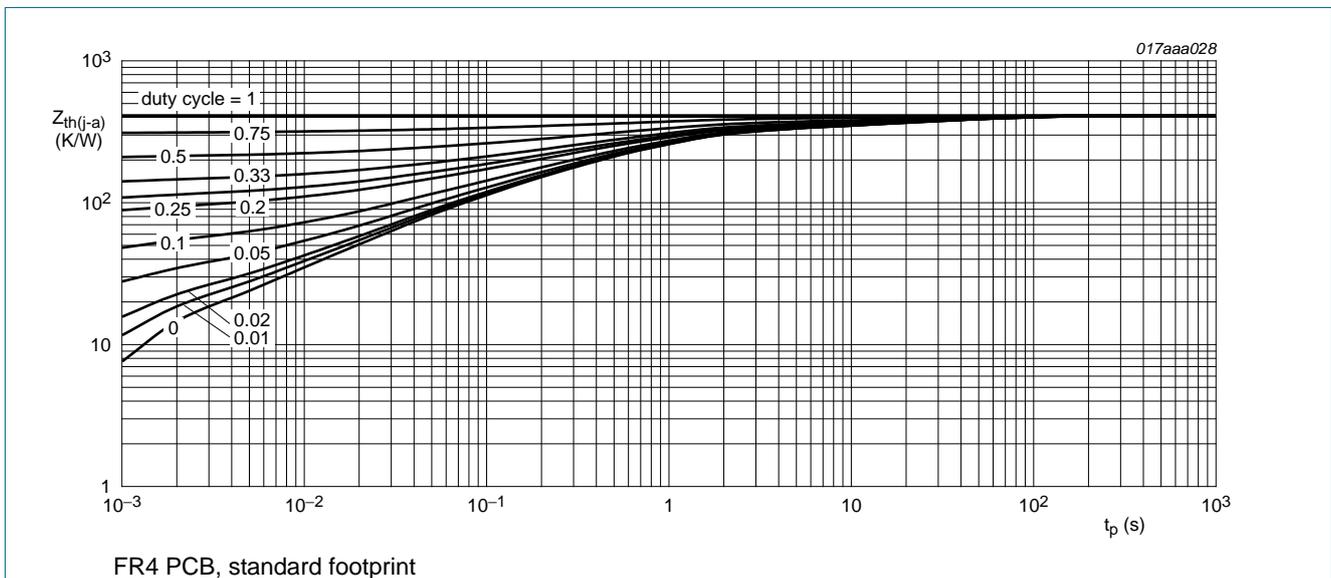
## 6. Thermal characteristics

**Table 6. Thermal characteristics**

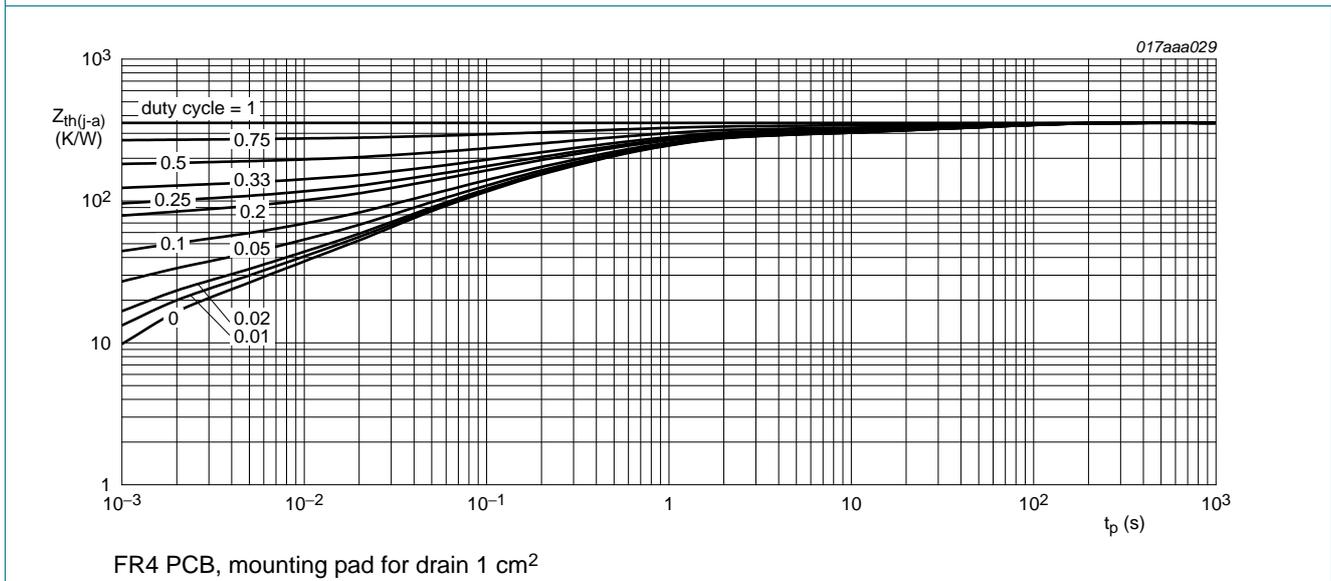
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	415	480	K/W
			[2]	-	350	400	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	150	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

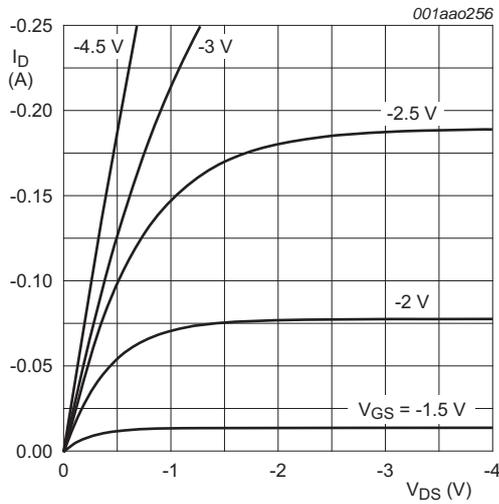


**Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

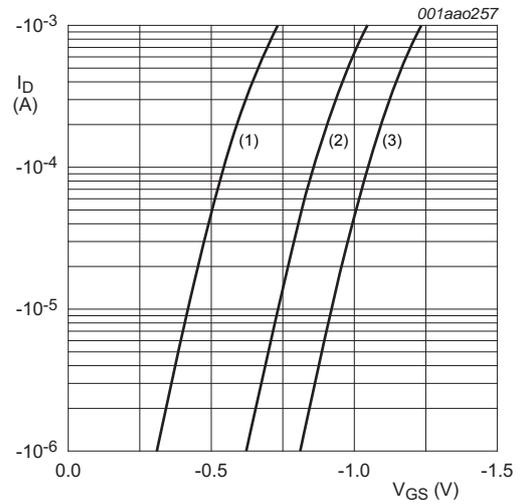
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu\text{A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu\text{A}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-0.6	-0.9	-1.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = -30 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 150 \text{ }^\circ\text{C}$	-	-	-10	$\mu\text{A}$
		$V_{DS} = -30 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	-1	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-0.2	-1	$\mu\text{A}$
		$V_{GS} = -8 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-0.2	-1	$\mu\text{A}$
		$V_{GS} = 4.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-10	-	nA
		$V_{GS} = -4.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-10	-	nA
		$V_{GS} = 2.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-1	-	nA
		$V_{GS} = -2.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-1	-	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}$ ; $I_D = -200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	2.8	4.1	$\Omega$
		$V_{GS} = -4.5 \text{ V}$ ; $I_D = -200 \text{ mA}$ ; $T_j = 150 \text{ }^\circ\text{C}$	-	5.3	7.8	$\Omega$
		$V_{GS} = -2.5 \text{ V}$ ; $I_D = -10 \text{ mA}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	5.3	6.5	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = -10 \text{ V}$ ; $I_D = -200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	160	-	mS
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -15 \text{ V}$ ; $I_D = -200 \text{ mA}$ ; $V_{GS} = -4.5 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	0.55	0.72	nC
$Q_{GS}$	gate-source charge		-	0.23	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -15 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	31	46	pF
$C_{oss}$	output capacitance		-	6.5	-	pF
$C_{rss}$	reverse transfer capacitance		-	2.3	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -20 \text{ V}$ ; $R_L = 250 \Omega$ ; $V_{GS} = -4.5 \text{ V}$ ; $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	19	38	ns
$t_r$	rise time		-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	65	130	ns
$t_f$	fall time		-	38	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = -200 \text{ mA}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-0.47	-0.88	-1.2	V



$T_j = 25\text{ }^\circ\text{C}$

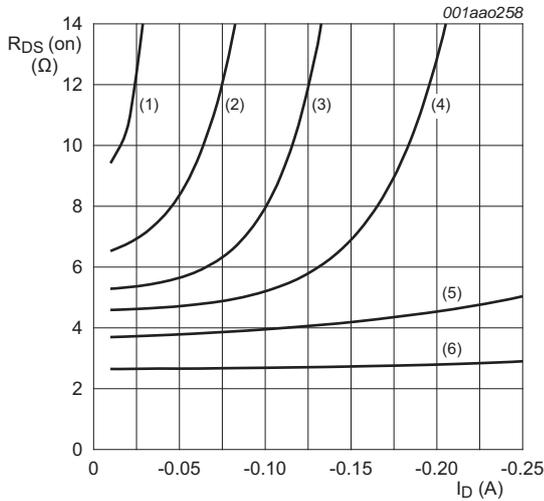
**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = -5\text{ V}$

- (1) minimum values
- (2) typical values
- (3) maximum values

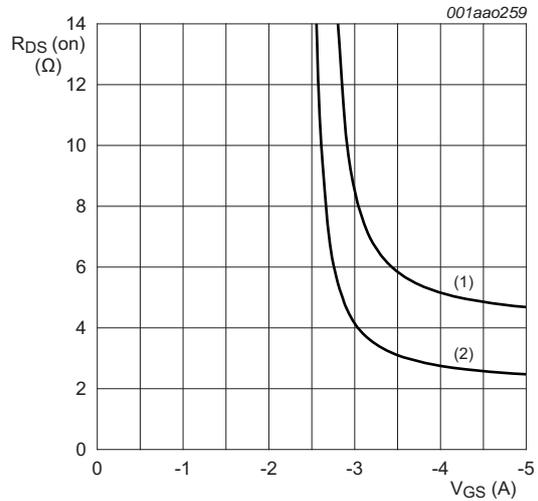
**Fig 7. Sub-threshold drain current as a function of gate-source voltage**



$T_j = 25\text{ }^\circ\text{C}$

- (1)  $V_{GS} = -1.75\text{ V}$
- (2)  $V_{GS} = -2.0\text{ V}$
- (3)  $V_{GS} = -2.25\text{ V}$
- (4)  $V_{GS} = -2.5\text{ V}$
- (5)  $V_{GS} = -3.0\text{ V}$
- (6)  $V_{GS} = -4.5\text{ V}$

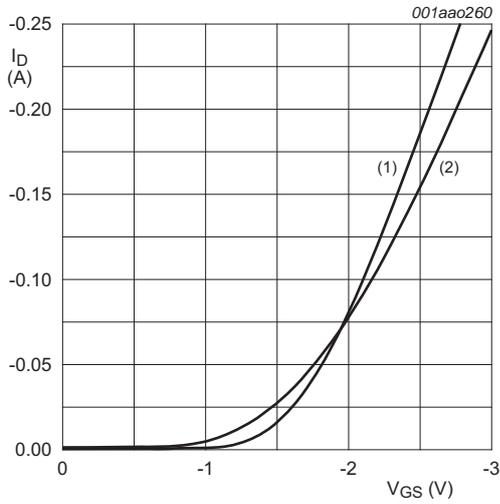
**Fig 8. Drain-source on-state resistance as a function of drain current; typical values**



$I_D = -200\text{ mA}$

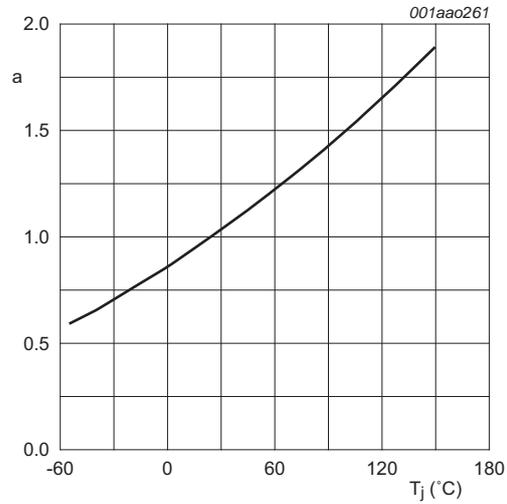
- (1)  $T_j = 150\text{ }^\circ\text{C}$
- (2)  $T_j = 25\text{ }^\circ\text{C}$

**Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**



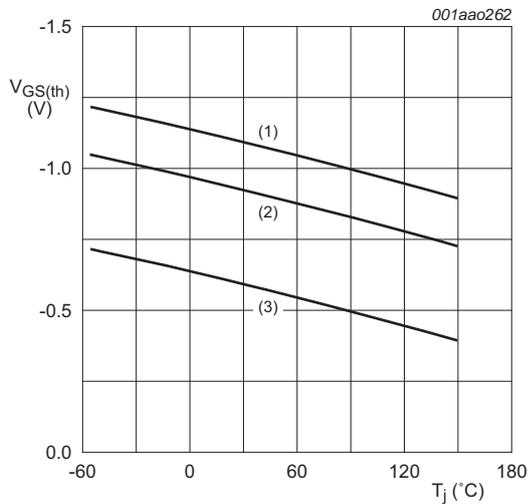
$V_{DS} > I_D \times R_{DS(on)}$   
 (1)  $T_j = 25\text{ °C}$   
 (2)  $T_j = 150\text{ °C}$

**Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



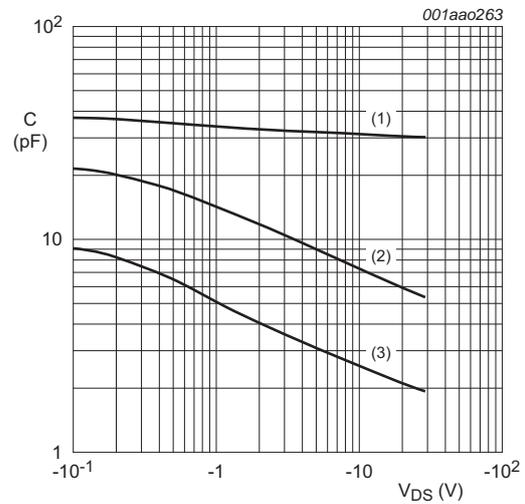
$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ C}}$$

**Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**



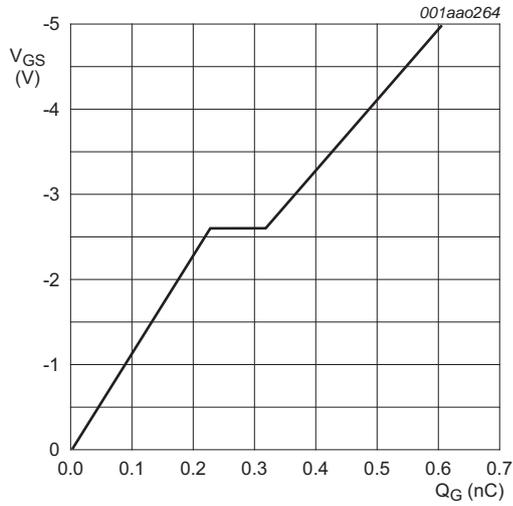
$I_D = -0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig 12. Gate-source threshold voltage as a function of junction temperature**



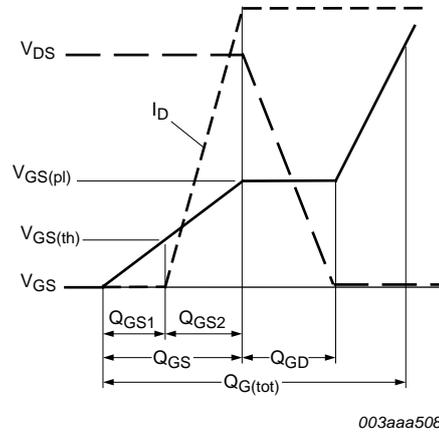
$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

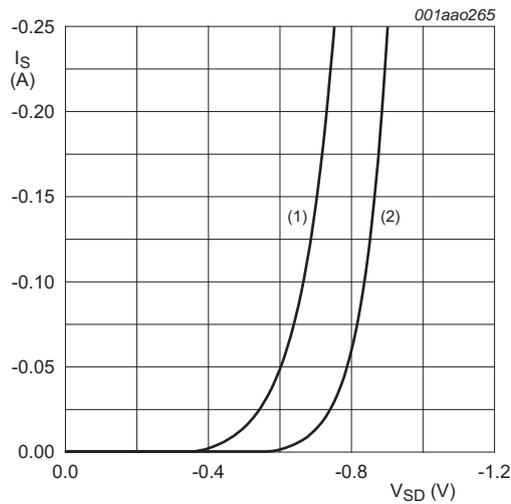


$I_D = -200 \text{ mA}; V_{DS} = -15 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



**Fig 15. Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$

**Fig 16. Source current as a function of source-drain voltage; typical values**

## 8. Test information

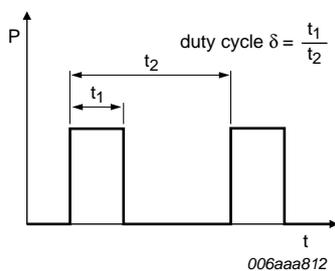


Fig 17. Duty cycle definition

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

**9. Package outline**

Plastic surface-mounted package; 3 leads

SOT323

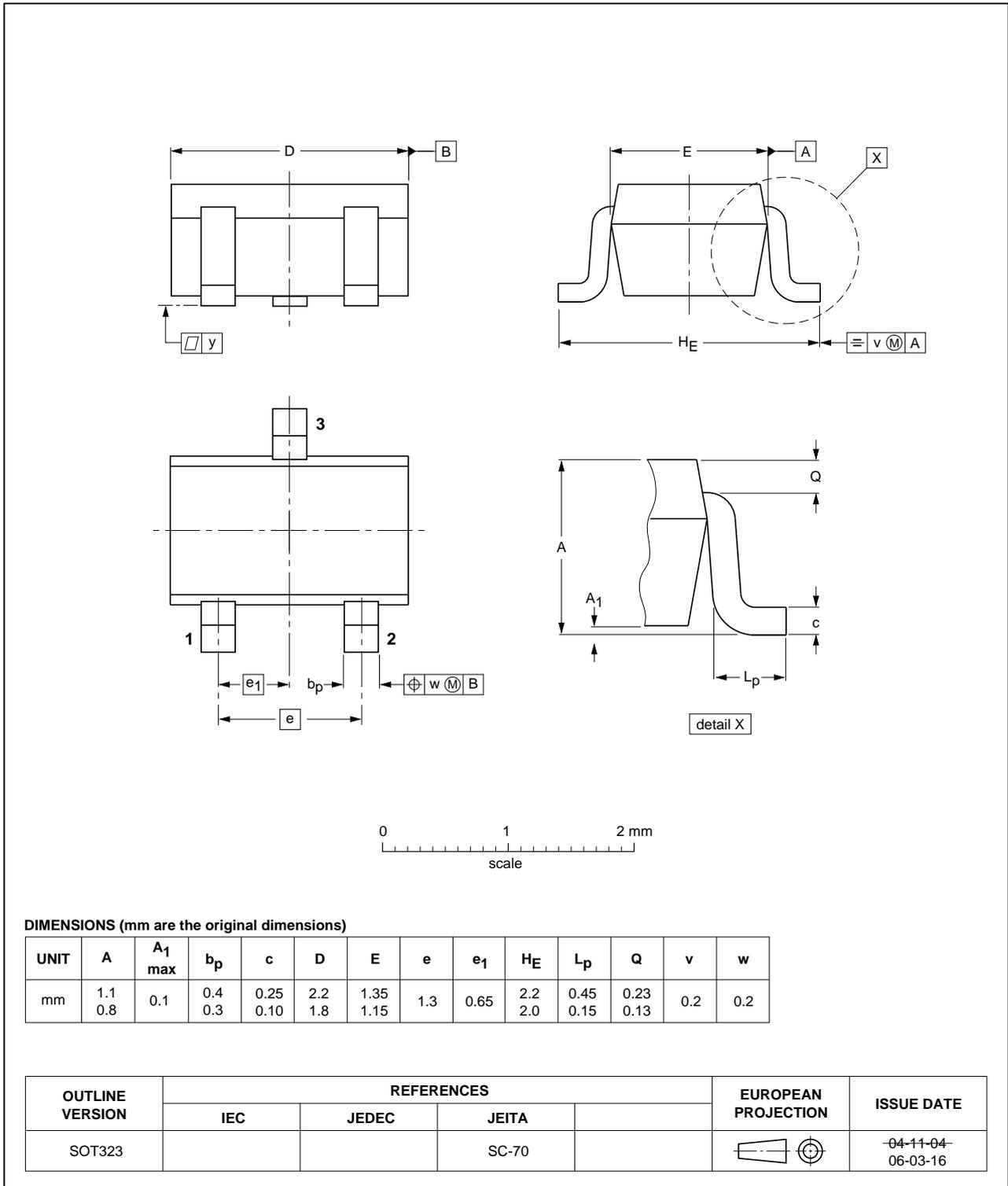
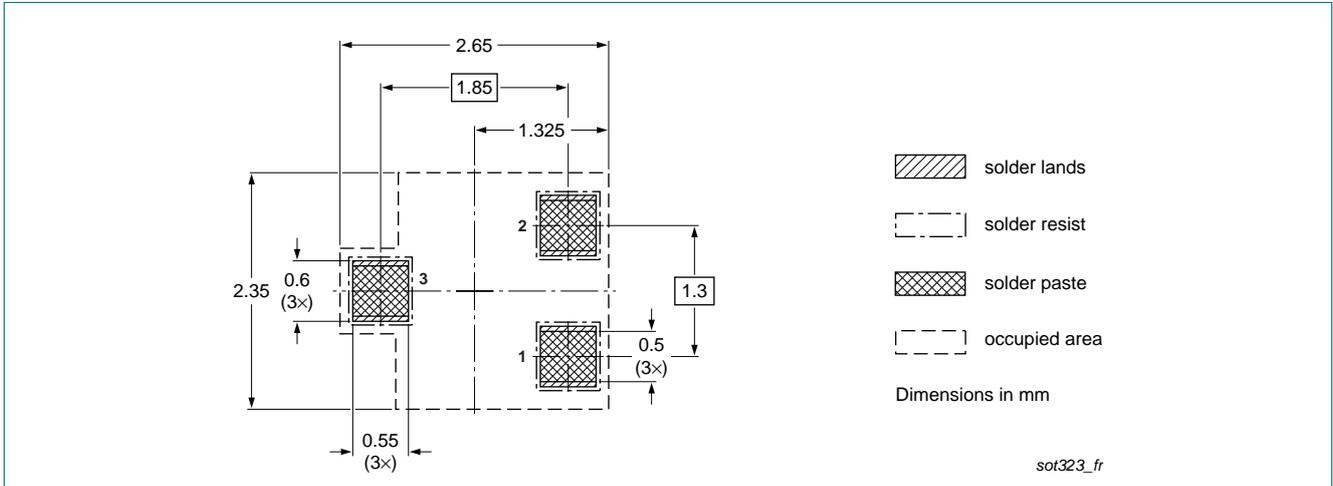
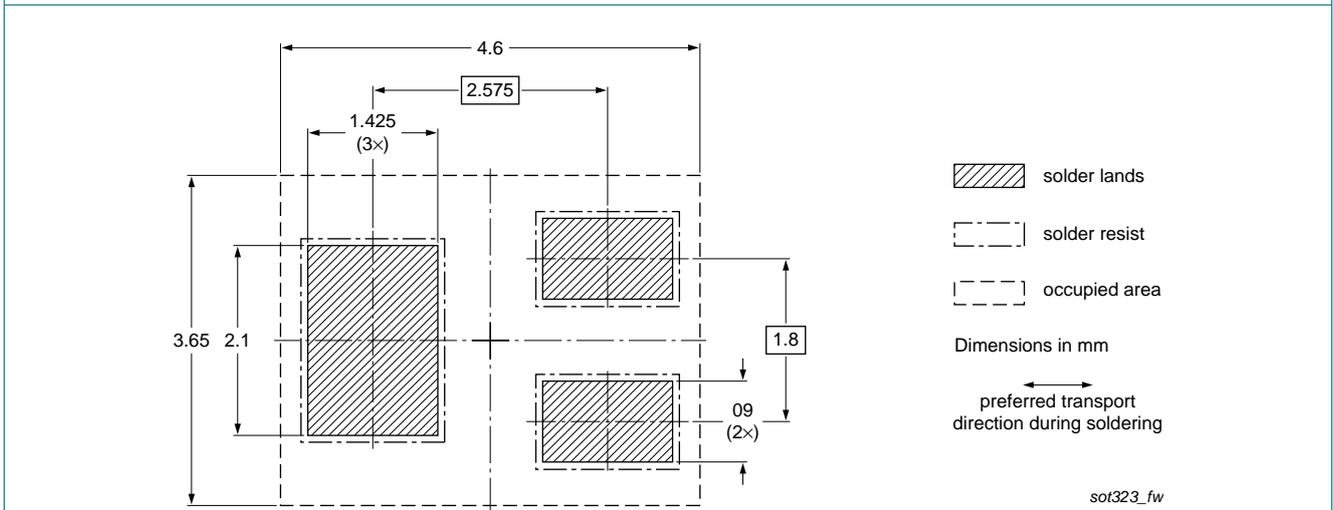


Fig 18. Package outline SOT323 (SC-70)

**10. Soldering**



**Fig 19. Reflow soldering footprint for SOT323 (SC-70)**



**Fig 20. Wave soldering footprint for SOT323 (SC-70)**

## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3008PBKW v.1	20110801	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <a href="#">[1]</a> <a href="#">[2]</a>	Product status <a href="#">[3]</a>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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